

OKI semiconductor

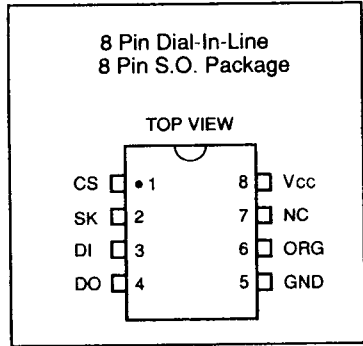
MSM16851

1,024-Bit SERIAL E²PROM

FEATURES:

- CMOS Floating Gate Technology
- Single +5-volt supply
- Eight pin plastic package
- 64 × 16 or 128 × 8 user selectable serial memory
- Compatible with CATALYST CAT93C46
- Self-timed programming cycle with Auto-erase
- Word and chip erasable
- Operating range 0°C to 70°C
- 10,000 erase/write cycles for each address
- 10 year data retention
- Power-up inadvertent write protection

PIN CONFIGURATION

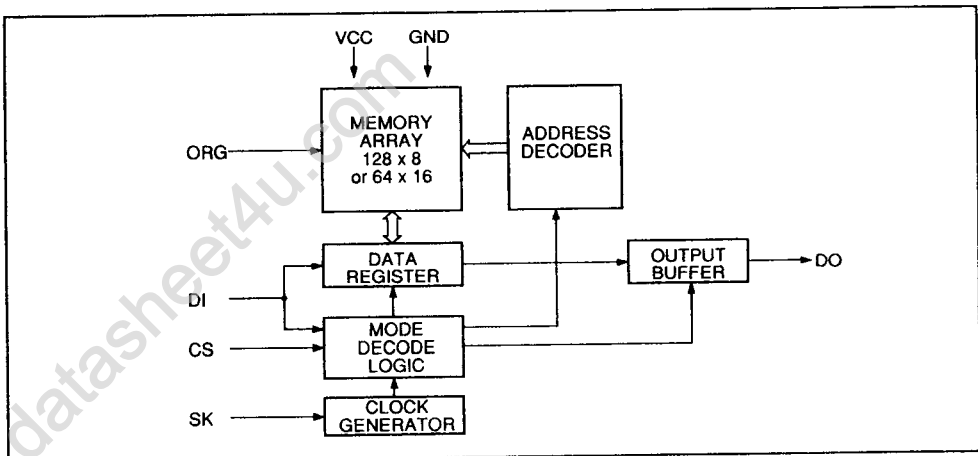


PIN FUNCTIONS

CS	Chip Select
SK	Clock Input
DI	Serial Data Input
DO	Serial Data Output
V _{cc}	+5 V Power Supply
NC	No Connection
GND	Ground

ORG Memory Array Organization Selection Input. When the ORG pin is connected to V_{cc} the 64 × 16 organization is selected. When it is connected to ground the 128 × 8 organization is selected. If the ORG pin is left unconnected, then an internal pull-up device will select the 64 × 16 organization.

BLOCK DIAGRAM



INSTRUCTION SET						
Instruction	Start Bit	Opcode	Address		Data	
			128 x 8	64 x 16	128 x 8	64 x 16
READ	1	1 0	A6-A0	A5-A0		
ERASE	1	1 1	A6-A0	A5-A0		
WRITE	1	0 1	A6-A0	A5-A0	D7-D0	D15-D0
EWEN	1	0 0	11xxxxx	11xxxx		
EWDS	1	0 0	00xxxxx	00xxxx		
ERAL	1	0 0	10xxxxx	10xxxx		
WRAL	1	0 0	01xxxxx	01xxxx	D7-D0	D15-D0

Power-On Data Protection Circuitry: During power-up, all modes of operation except READ mode are inhibited until Vcc reaches a level of approximately 3.5 V. During power-down, the source data protection circuitry inhibits all modes except READ mode when Vcc falls below the voltage range of approximately 3.5 V.

ELECTRICAL CHARACTERISTICS

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Value	Unit
Supply Voltage	V _{CC}	Ta = 25°C	-0.3 ~ 7	V
Input Voltage	V _I		-0.3 ~ V _{CC} + 0.3	V
Output Voltage	V _O		-0.3 ~ V _{CC} + 0.3	V
Storage Temperature	T _{STG}		-55 ~ +150	°C

Note: Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as recommended. Exposure to ABSOLUTE MAXIMUM RATINGS for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE

Parameter	Symbol	Range	Unit
Supply Voltage	V _{CC}	5 ± 10%	V
Temperature Range	Ta	0 ~ 70	°C
Data Hold Temperature	Ta	0 ~ 70	°C

DC CHARACTERISTICS

(V_{CC} = 4.5V to 5.5V, Ta = 0°C ~ 70°C, unless otherwise specified.)

Parameter	Symbol	Condition	Min	Max	Unit
Supply Voltage	V _{CC}		4.5	5.5	V
Power Supply Current	I _{CC1}	V _{CC} = 5.0V CS = 5.0V DI = SK = 0.0V or V _{CC} DO = OPEN		3	mA
	I _{CC2}	V _{CC} = 5.5 V CS = 0 DO = ORG = OPEN DI = 0 SK = 0		100	μA
"L" Input Voltage	V _{IL}		-0.1	0.8	V
"H" Input Voltage	V _{IH}		2.0	V _{CC} +1	V
"L" Output Voltage	V _{OL}	I _{OL} = 2.1mA		0.4	V
"H" Output Voltage	V _{OH}	I _{OH} = -400μA	2.4		V
Input Leakage Current	I _{LI}	V _{in} = V _{CC} +0.1V		10	μA
Output Leakage Current	I _{LO}	V _{out} = V _{CC} CS = 0		10	μA

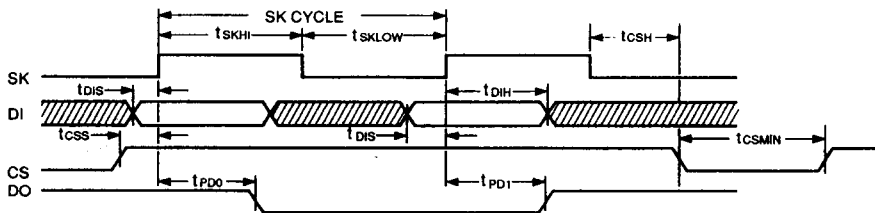
AC CHARACTERISTICS

($V_{CC} = 4.5V \sim 5.5V$, $T_a = 0^\circ C \sim 70^\circ C$)

Parameter	Description	Test Condition	Min	Typ	Max	Unit
t _{CSS}	CS Set up Time		50			ns
t _{CSH}	CS Hold Time		0			ns
t _{DIS}	DI Setup Time		100			ns
t _{DIH}	DI Hold Time		100			ns
t _{PD1}	Output Delay to 1	C _L = 100pF V _{OL} = 0.8V, V _{OH} = 2.0V V _{IL} = 0.45V, V _{IH} = 2.4V			500	ns
t _{PD0}	Output Delay to 0				500	ns
t _{HZ}	Output Delay to HiZ			100		ns
t _{EW}	Erase / Write Pulse Width				10	ms
t _{CSMIN}	Min CS Low Time		250			ns
t _{SKHI}	Min SK High Time		250			ns
t _{SKLOW}	Min SK Low Time		250			ns
t _{SV}	Output Delay to Status Valid	C _L = 100 pF				ns
SK _{MAX}	Maximum Frequency		DC		700	kHz

Synchronous Timing

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DEVICE OPERATION

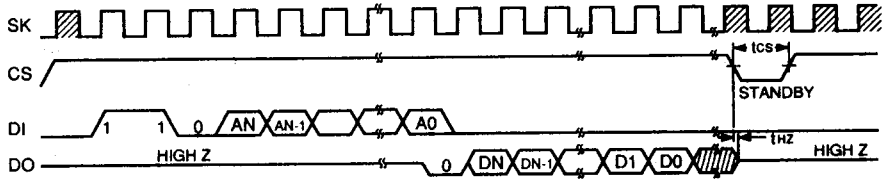
The MSM16851 has 7 instructions that allow it to read, erase, or write. Each instruction consists of a start bit logical 1, an opcode field (2 bits or 4 bits) and an address field (6 or 7 bits).

The DO pin is a multiplexed pin. It is used as Data Out during the Read mode. It can also be used as a Ready Busy status indicator in programming mode. In all the other modes DO is tri-stated.

During power-up, all modes of operation are disabled and the device comes up in a program disabled state. An EWEN instruction must be issued before starting to program.

At power-down, when V_{CC} falls below a level of approximately 3.5 V, the data protection circuitry inhibits operation, except READ mode, and an EWDS instruction is executed internally.

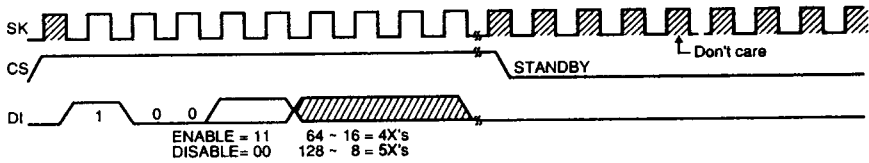
READ



Organization	AN	DN
128 × 8	A6	D7
64 × 16	A5	D15

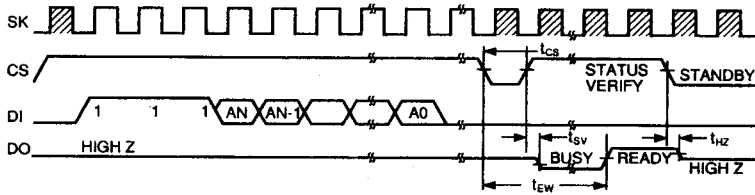
The READ instruction reads the contents of the addressed register. It outputs data serially on the DO pin. After the instruction is decoded, a dummy bit (logical 0) precedes the output data string.

EWEN/EWDS (Erase Write Enable/Erase Write Disable)



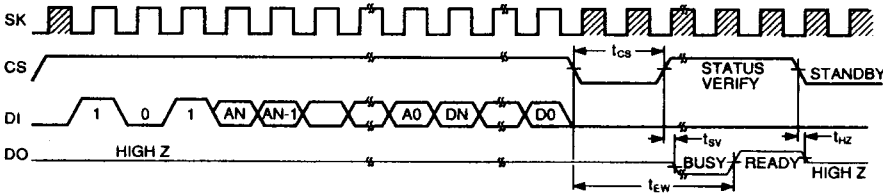
After power-up and before starting any programming instruction, the EWEN instruction must be issued. Once it is issued, it remains active until an EWDS instruction takes place. The EWDS instruction prevents accidental programming of the part. The READ instruction is independent from the EWEN and EWDS instructions.

ERASE



After an ERASE instruction is shifted in. CS is dropped low. This sets the beginning of the self timed erase sequence. If CS is then brought high (after observing t_{CS} spec) the DO pin acts as a status indicator. It remains low so long as the chip is programming. It goes high after all the bits of the addressed register are set to a logical 1.

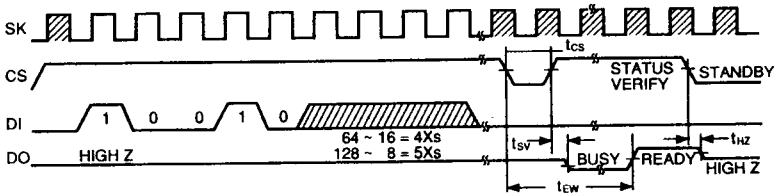
WRITE



After a WRITE instruction is shifted in with the corresponding 8 bits or 16 bits of data, CS is dropped low. This sets the beginning of the self timed programming sequence. If CS is brought high during the programming time (after observing the t_{CS} specification), the DO pin acts as a status indicator – it remains low so long as the chip is programming. It goes high after all the bits of the addressed register are set to their proper values. With the MSM16851 it is not necessary to erase a memory location before the WRITE instruction.

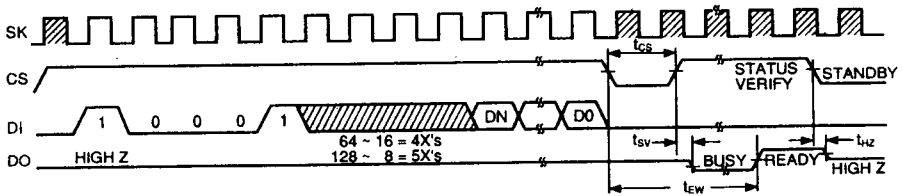
Organization	AN	DN
128 × 8	A6	D7
64 × 16	A5	D15

ERAL (Erase All)



The ERAL instruction erases the whole chip. Except for its different opcode, the ERAL instruction is identical to the ERASE instruction.

WRAL (Write All)



The WRAL instruction writes to all the registers simultaneously. All the registers must be erased before a WRAL operation. Except for its different opcode, the WRAL instruction is identical to the WRITE instruction.